



CPH6615 — N-Channel and P-Channel Silicon MOSFETs

General-Purpose Switching Device Applications

Features

- The CPH6615 incorporates a N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance, Ultrahigh-speed switching, thereby enabling high-density mounting.
- Excellent ON-resistance characteristic.
- Best suited for load switches.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		30	-30	V
Gate-to-Source Voltage	V _{GSS}		±20	±20	V
Drain Current (DC)	I _D		2.5	-1.8	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	10	-7.2	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (90mm²X0.8mm)1unit	0.9		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =30V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _D =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _D =10V, I _D =1.5A	1.2	2.0		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1.5A, V _{GS} =10V		79	105	mΩ
	R _{DS(on)2}	I _D =1A, V _{GS} =4V		150	210	mΩ
Input Capacitance	C _{iss}	V _D =10V, f=1MHz		187		pF
Output Capacitance	C _{oss}	V _D =10V, f=1MHz		40		pF
Reverse Transfer Capacitance	C _{rss}	V _D =10V, f=1MHz		33		pF

Marking : WB

Continued on next page.

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CPH6615

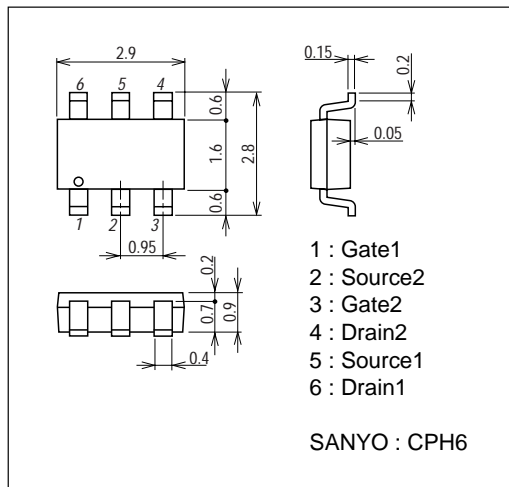
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7.8		ns
Rise Time	t_r	See specified Test Circuit.		18.5		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		22		ns
Fall Time	t_f	See specified Test Circuit.		12		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		5.2		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		1		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		0.97		nC
Diode Forward Voltage	V_{SD}	$I_S=2.5A, V_{GS}=0$		0.9	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-1A$	1.1	1.8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-1A, V_{GS}=-10V$		180	235	$m\Omega$
	$R_{DS(on)2}$	$I_D=-0.5A, V_{GS}=-4V$		320	450	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		226		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		43		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		36		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		8.5		ns
Rise Time	t_r	See specified Test Circuit.		10.5		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		29		ns
Fall Time	t_f	See specified Test Circuit.		22		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-1.8A$		5.5		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-1.8A$		1		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-1.8A$		0.97		nC
Diode Forward Voltage	V_{SD}	$I_S=-1.8A, V_{GS}=0$		-0.91	-1.5	V

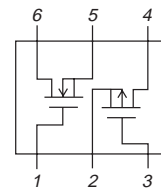
Package Dimensions

unit : mm

2238



Electrical Connection

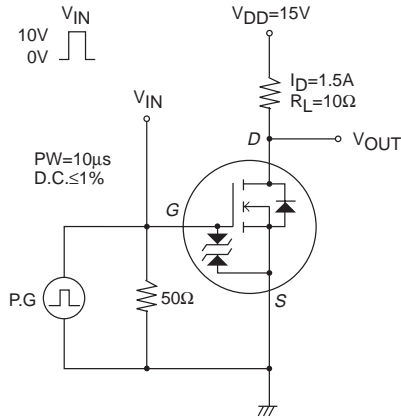


- 1 : Gate1
- 2 : Source2
- 3 : Gate2
- 4 : Drain2
- 5 : Source1
- 6 : Drain1

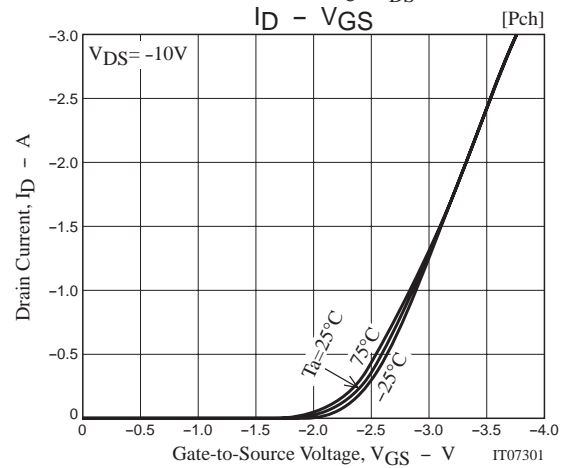
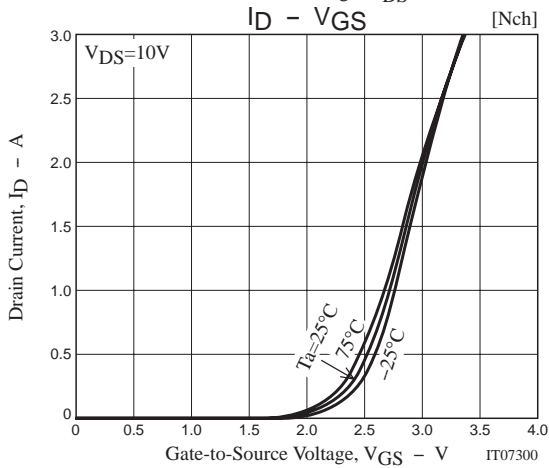
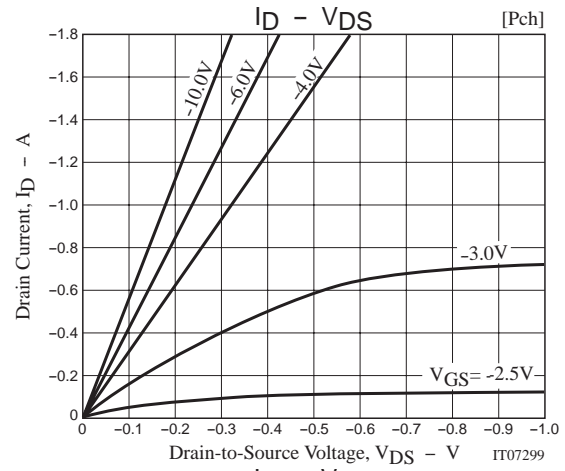
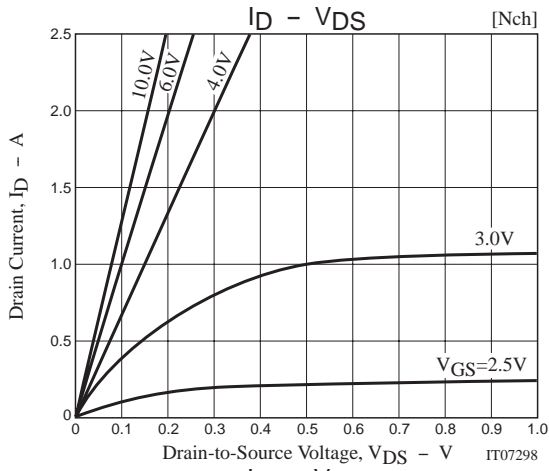
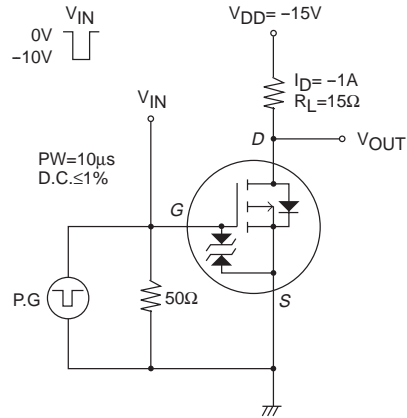
Top view

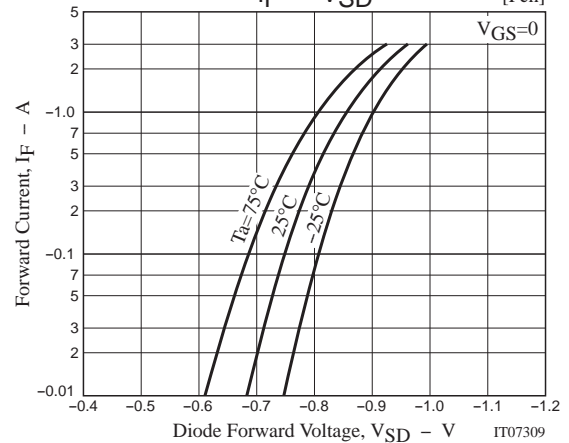
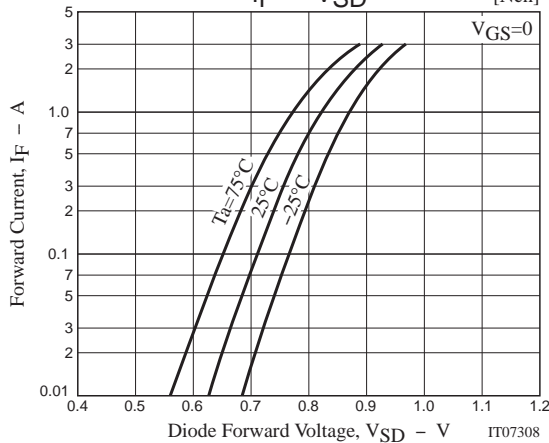
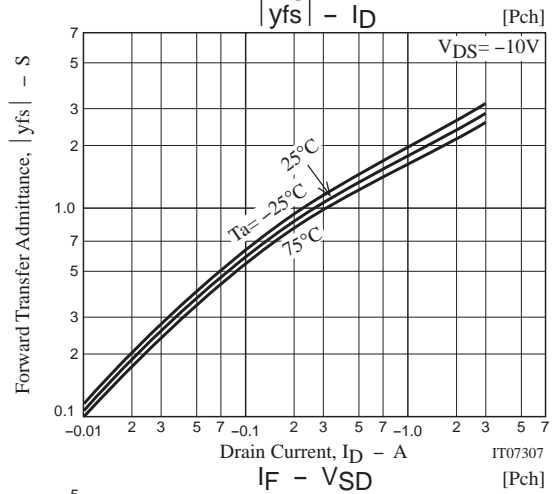
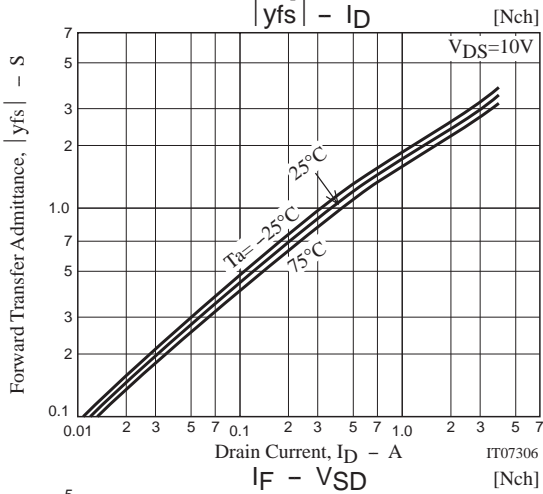
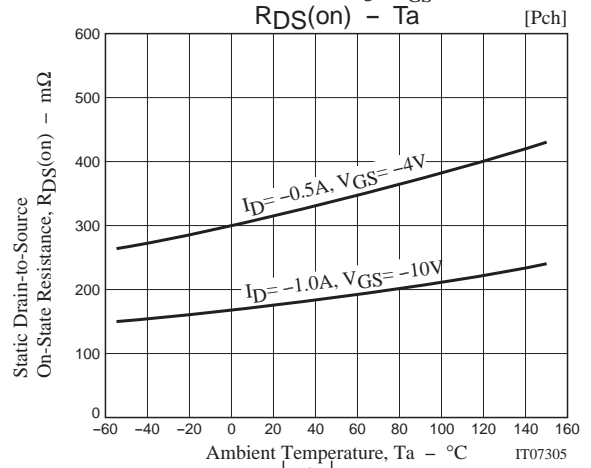
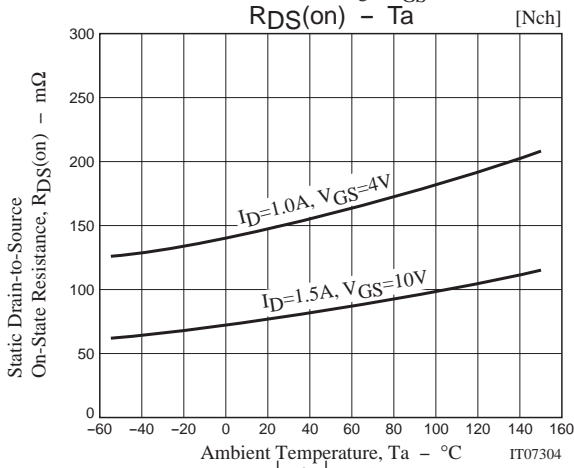
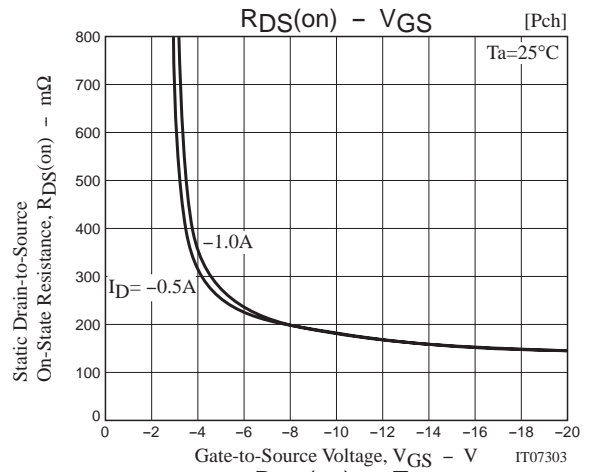
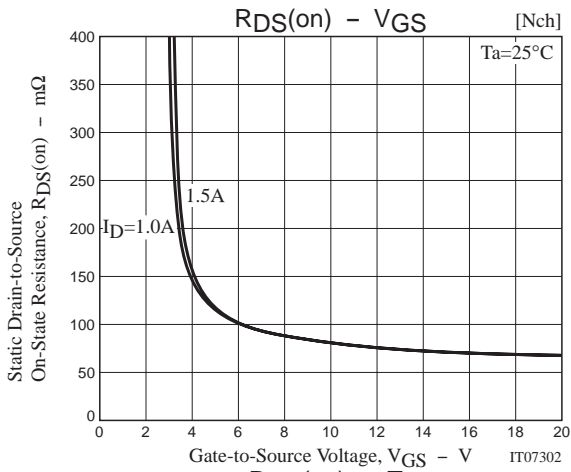
Switching Time Test Circuit

[N-channel]

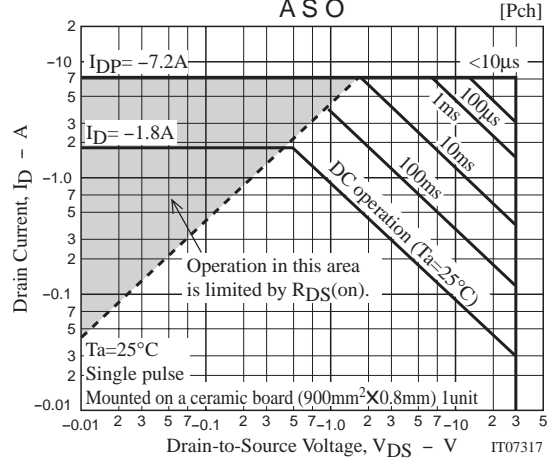
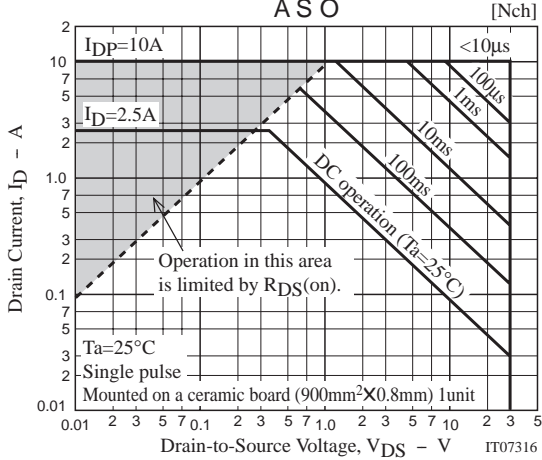
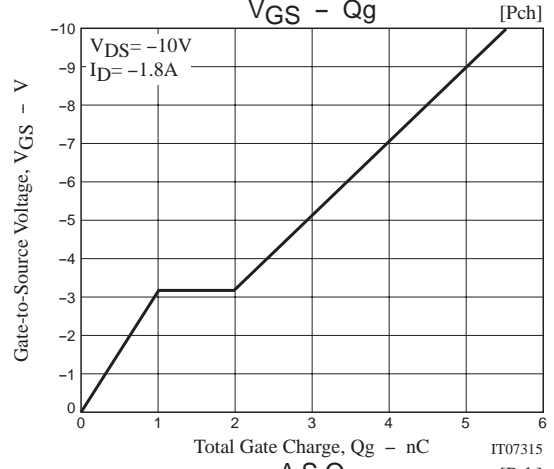
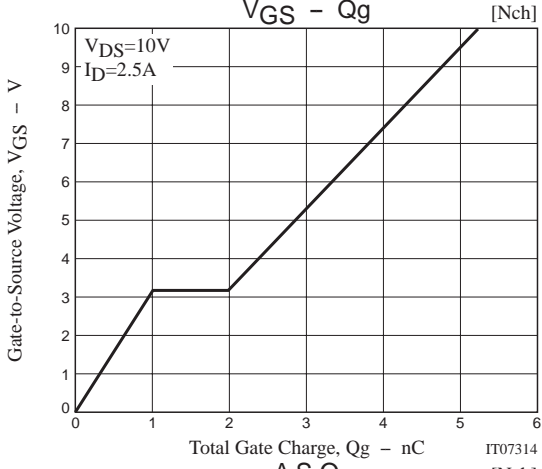
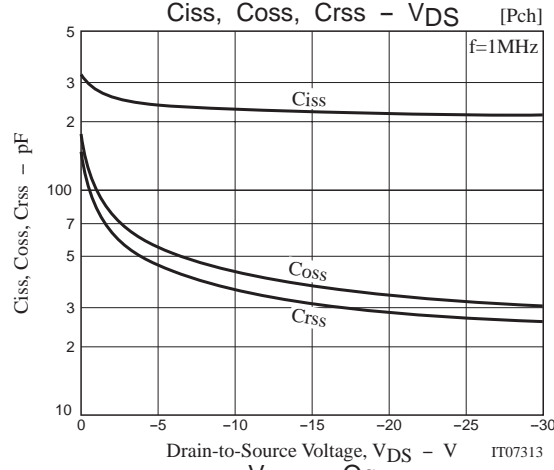
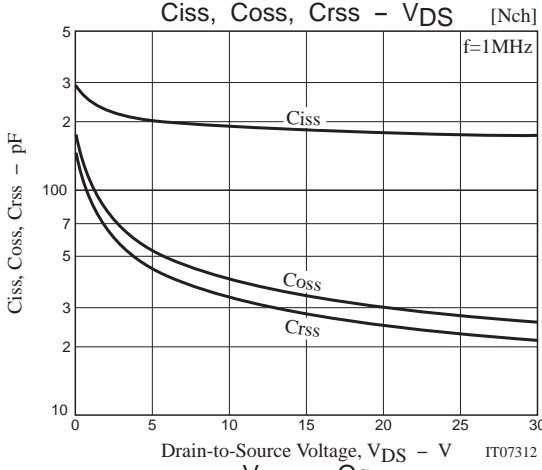
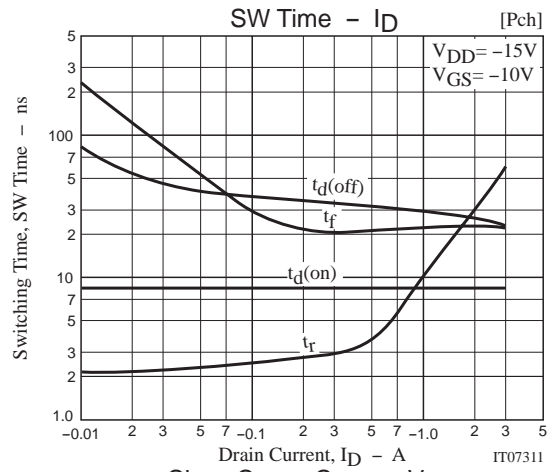
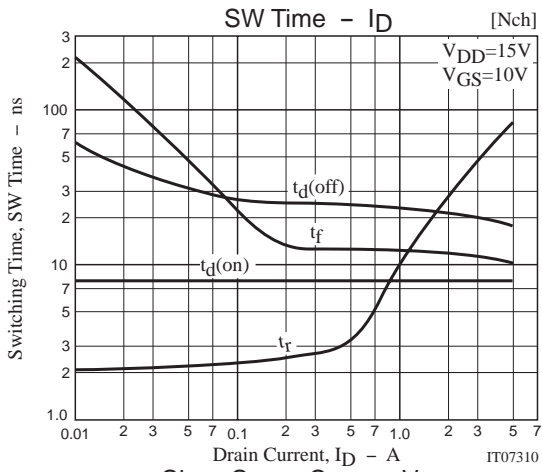


[P-channel]

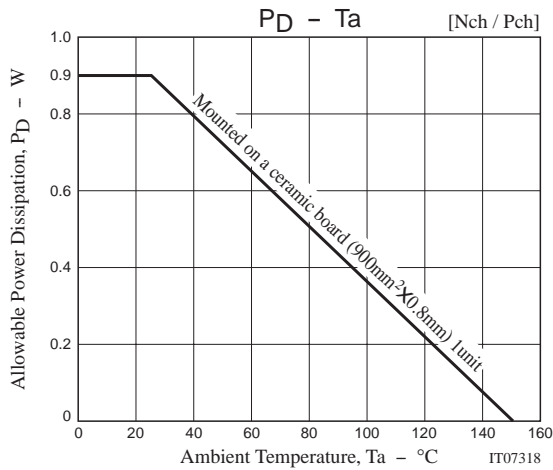




CPH6615



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Note on usage : Since the CPH6615 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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